Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2-\pi$ -MOSV)

# **2SJ349**

# DC-DC Converter, Relay Drive and Motor Drive Applications

• 4-V gate drive

• Low drain-source ON-resistance :  $RDS(ON) = 33 \text{ m}\Omega \text{ (typ.)}$ 

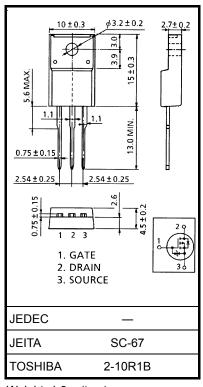
• High forward transfer admittance  $|Y_{fs}| = 20 \text{ S (typ.)}$ 

• Low leakage current :  $IDSS = -100 \mu A (max) (VDS = -60 V)$ 

• Enhancement mode:  $V_{th} = -0.8$  to -2.0 V ( $V_{DS} = -10$  V,  $I_{D} = -1$  mA)

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteris                                  | stics         | Symbol           | Rating     | Unit |
|--|---------------|------------------|------------|------|
| Drain-source voltage                         |               | $V_{DSS}$        | -60        | V    |
| Drain-gate voltage (R <sub>GS</sub> = 20 kΩ) |               | $V_{DGR}$        | -60        | V    |
| Gate-source voltage                          |               | $V_{GSS}$        | ±20        | V    |
| Drain current                                | DC (Note 1)   | I <sub>D</sub>   | -20        | Α    |
|  | Pulse(Note 1) | I <sub>DP</sub>  | -80        | Α    |
| Drain power dissipation                      | n (Tc = 25°C) | $P_{D}$          | 45         | W    |
| Single pulse avalanche energy (Note 2)       |               | E <sub>AS</sub>  | 800        | mJ   |
| Avalanche current                            |               | I <sub>AR</sub>  | -20        | Α    |
| Repetitive avalanche energy (Note 3)         |               | E <sub>AR</sub>  | 4.5        | mJ   |
| Channel temperature                          |               | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature range                    |               | T <sub>stg</sub> | -55 to 150 | °C   |



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = -50 V,  $T_{ch}$  = 25°C (initial), L = 1.44 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = -20 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



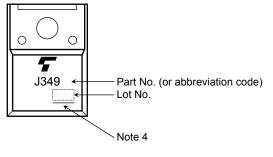
## **Electrical Characteristics (Ta = 25°C)**

| Charac  | cteristics      | Symbol               | Test Condition   | Min  | Тур. | Max  | Unit |
|---|-----------------|----------------------|--|------|------|------|------|
| Gate leakage cu                                 | irrent          | I <sub>GSS</sub>     | V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V   | _    | _    | ±10  | μΑ   |
| Drain cut-off cu                                | rrent           | I <sub>DSS</sub>     | V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V   | _    | _    | -100 | μΑ   |
| Drain-source br                                 | eakdown voltage | V (BR) DSS           | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V   | -60  | _    | _    | V    |
| Gate threshold v                                | oltage/         | V <sub>th</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA  | -0.8 | _    | -2.0 | V    |
| Drain-source ON-resistance                      |                 | R <sub>DS (ON)</sub> | V <sub>GS</sub> = -4 V, I <sub>D</sub> = -10 A   | _    | 50   | 90   | mO   |
|   |                 |                      | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -10 A  | _    | 33   | 45   | mΩ   |
| Forward transfe                                 | r admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A  | 10   | 20   | _    | S    |
| Input capacitano                                | e               | C <sub>iss</sub>     |  | _    | 2800 | _    |      |
| Reverse transfe                                 | r capacitance   | C <sub>rss</sub>     | $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$  | _    | 450  | _    | pF   |
| Output capacitance                              |                 | Coss                 |  | _    | 1300 | _    |      |
| Switching time                                  | Rise time       | t <sub>r</sub>       | $V_{GS} \stackrel{0V}{\longrightarrow} I_{D} = -10A \\ \downarrow V_{OUT} \stackrel{1}{\longrightarrow} R_{L} = 3\Omega \\ \downarrow V_{DD} = -30V$ | _    | 15   | _    | ns   |
|   | Turn-on time    | t <sub>on</sub>      |  | _    | 35   | _    |      |
|   | Fall time       | t <sub>f</sub>       |  | _    | 25   | _    |      |
|   | Turn-off time   | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_{\rm W} = 10 \mu \rm s$   | _    | 120  | _    |      |
| Total gate charge (Gate-source plus gate-drain) |                 | Qg                   |  |      | 90   | _    |      |
| Gate-source charge                              |                 | Q <sub>gs</sub>      | $V_{DD} \approx -48 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$  |      | 65   |      | nC   |
| Gate-drain ("miller") charge                    |                 | Q <sub>gd</sub>      |  | _    | 25   |      |      |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _   | _   | _    | -20 | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _   | _   | _    | -80 | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = -20 A, V <sub>GS</sub> = 0 V  | _   | _    | 1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = -20 A, V <sub>GS</sub> = 0 V, |     | 75   | _   | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> / dt = 50 A / µs               | _   | 83   | _   | nC   |

## Marking

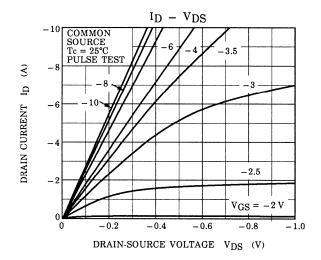


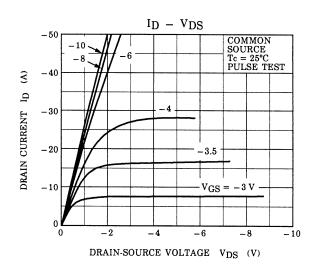
Note 4: A line under a Lot No. identifies the indication of product Labels.

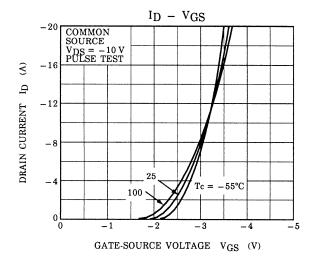
Not underlined: [[Pb]]/INCLUDES > MCV

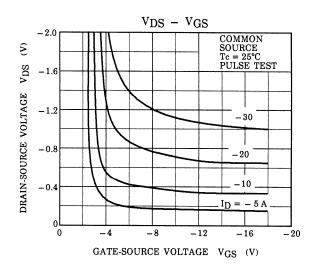
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

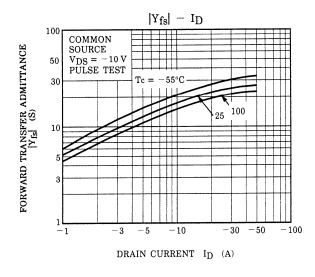
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

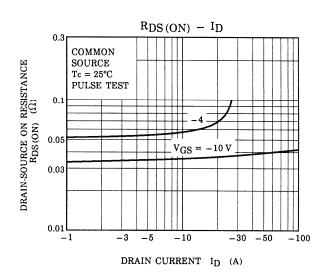




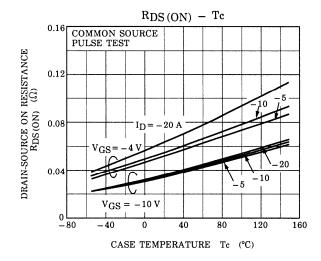


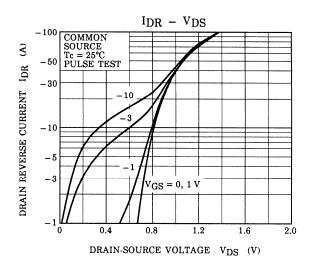


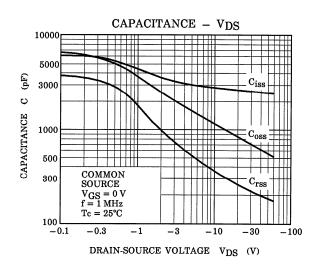


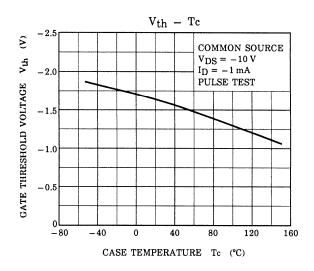


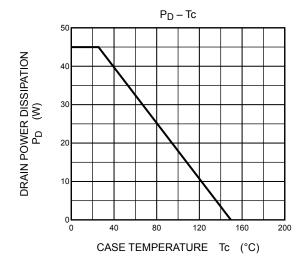
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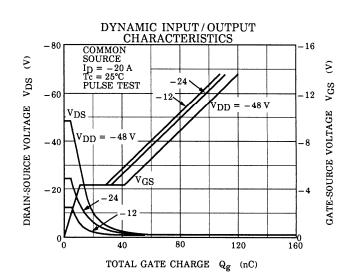


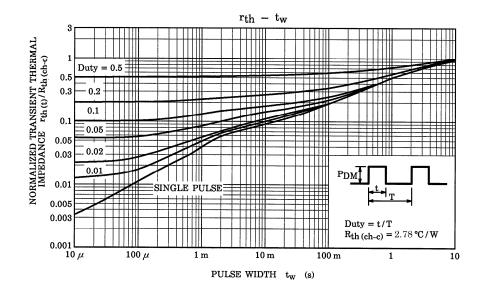


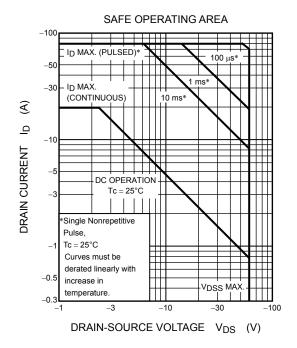


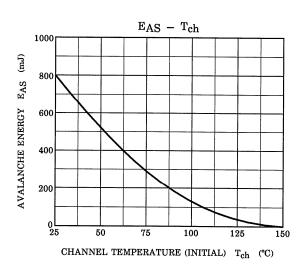


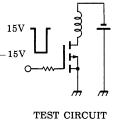


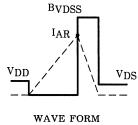












 $R_G = 25\Omega$  $V_{DD} = -50V$ , L=1.44mH

$$E_{\text{AS}} = \frac{1}{2} \cdot L \cdot I^2 \cdot (\frac{B_{\text{VDSS}}}{B_{\text{VDSS}} - V_{\text{DD}}})$$

5 2009-12-10

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